

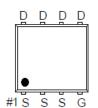
-30V P-Channel Power MOSFET

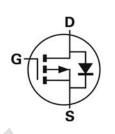
V_{DSS}, -30V

 $R_{DS(ON)}$, $20m\Omega$ (max.) @ $V_{GS} \text{=-}10V$ $R_{DS(ON)}$, $33m\Omega$ (max.) @ $V_{GS} \text{=-}4.5V$

I_D ,-51.3A

PDFN 3.3x3.3-8L





Description

The SGP3015E uses advanced Trench technology and designs to provide excellent $R_{\text{DS}(\text{ON})}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

- Low On-Resistance
- · Low Input Capacitance
- Low Miller Charge
- Low Input / Output Leakage
- · Pb-free lead plating; RoHS compliant

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch
- DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGP3015E	Halogen-Free	PDFN 3.3x3.3-8L	E	Tape & Reel	5,000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Paramete	r	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±20	V
Droin Current Centinuous	T _C =25°C	I-	-51.3	Α
Drain Current-Continuous	T _C =100°C	l _D	-32.4	Α
Drain Current-Pulsed Note 1		I _{DM}	-89	А
Avalanche Current, L=0.1mH		las	-20	Α
Avalanche Energy, L=0.1mH Note 3		Eas	20	mJ
Maximum Dowar Discipation	T _C =25°C	D-	7.9	W
Maximum Power Dissipation	Tc=100°C	P _D	3.2	W
Operating Junction Temperature Range		TJ	150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Thermal resistance, Junction-to-Ambient Note 2	R _{θJA}	Steady State	ı	53		°C/W
Thermal resistance, Junction-to-Case Note 2	Rejc	Steady State	=	15.8		°C/W

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-30V P-Channel Power MOSFET

Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250µA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =-250µA	-1	-1.5	-2.5	V
Drain-Source On-State Resistance	В	V _{GS} =-10V, I _{DS} =-8A	-	-	20	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _{DS} =-6A	-		33	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss			1571	-	
Output Capacitance	Coss	V _{DS} =-15V, V _{GS} =0V, f=1MHz	-/\	180	-	pF
Reverse Transfer Capacitance	Crss		-	132	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	7.2	-	
Rise Time	tr	V _{DD} =-15V, V _{GS} =-10V,	-	40.2	-]
Turn-Off Delay Time	T _{d(off)}	$R_G=3\Omega$, $I_D=-15A$	-	45.6	-	ns
Fall Time	t _f		-	28.6	-	
Total Gate Charge at 10V	Qg	V 45V L 45A	-	11.8	-	
Gate to Source Gate Charge	Qgs	V _{DS} =-15V, I _{DS} =-15A, V _{GS} =-4.5V	-	6.5	-	nC
Gate to Drain "Miller" Charge	Q _{gd}		-	3.5	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-15A	-	-	-1.2	V
Body Diode Reverse Recovery Time	trr	1 - 454 - 41/-14-4004/	-	12.8	-	ns
Body Diode Reverse Recovery Charge	Qrr	- I _F =-15A, dl/dt=100A/μs	-	3.3	-	nC
Reverse Recovery Current	IRRM	V _{DD} =-15V,I _F =-5A,di/dt=100A/μs		0.5		Α

Notes:

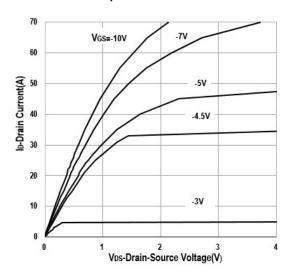
- 1. Pulse Test: Pulse Width ≤ 10ms, Duty Cycle ≤ 1%.
- 2. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Reja is guaranteed by design while Reja is determined by the user's board design. Reja shown below for single device operation on FR-4 in still air.

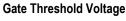


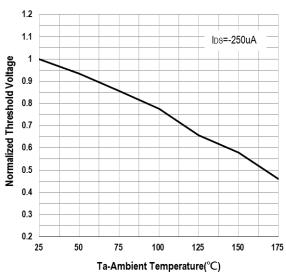
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Typical Operating Characteristics

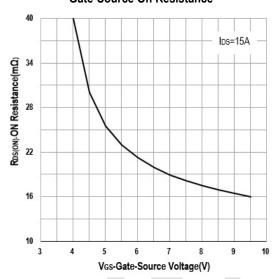
Output Characteristics

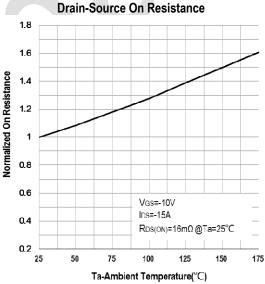




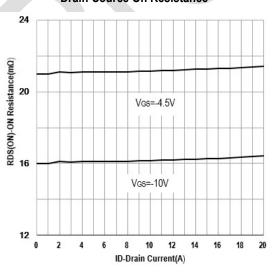


Gate-Source On Resistance

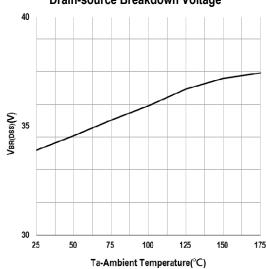




Drain-Source On Resistance



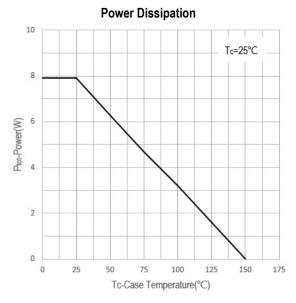
Drain-source Breakdown Voltage

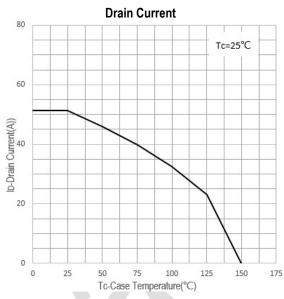


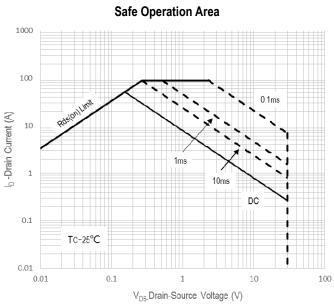


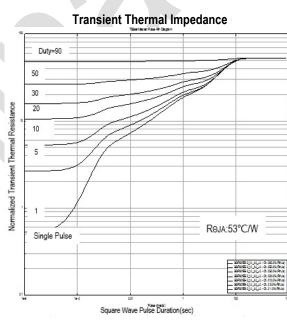
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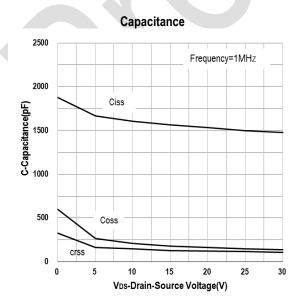
Typical Operating Characteristics (Cont.)

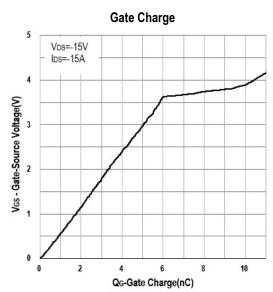












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Marking Information

PDFN 3.3x3.3-8L (E)	Marking Rule
Laser Marking	<u>Line 1</u> : Device Name
	P3015E
	Line 2 : Date Code
P3015E	YMMXXX
1 30102	
_ YMMXXX	Y: Year Code
•	MM: Month Code
	XXX : Serial Number
Diagram	Year Code Description As Below

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Year Code Description

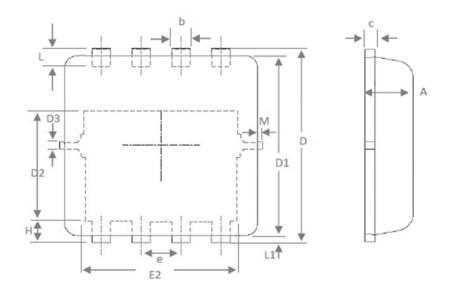
Year Code	Ye	ar
0	2010	2020
1	2011	2021
2	2012	2022
3	2013	2023
4	2014	2024
5	2015	2025
6	2016	2026
7	2017	2027
8	2018	2028
9	2019	2029

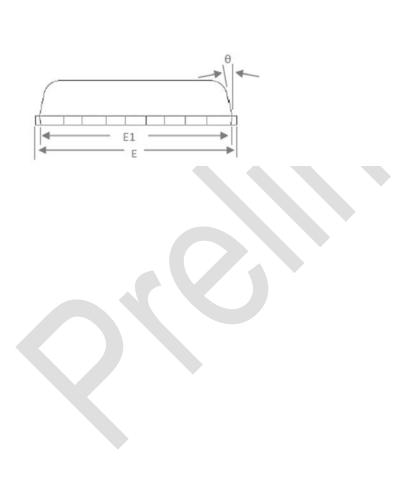






Package of Dimension





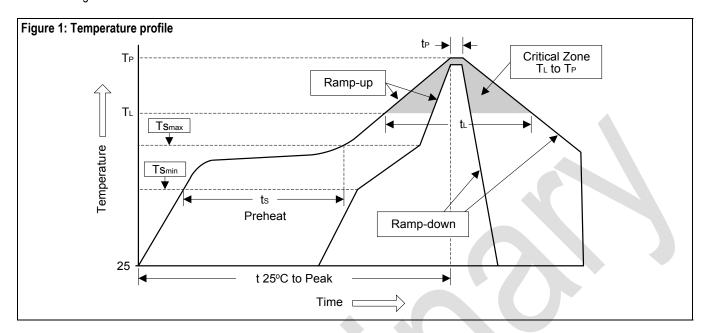
Symbol	Min	Nor	Max
Α	0.70	0.75	0.80
b	0.25	0.30	0.35
С	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	-	0.13	-
E	3.00	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
е		0.65BSC	3
Н	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
θ	-	10°	12°
М			0.15



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Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec	
Preheat			
- Temperature Min (Ts _{min})	100°C	150°C	
- Temperature Max (Ts _{max})	150°C	200°C	
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec	
Tsmax to T _L			
- Ramp-up Rate	<3°C/sec	<3°C/sec	
Time maintained above:			
- Temperature (T∟)	183°C	217°C	
- Time (t∟)	60 to 150 sec	60 to 150 sec	
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C	
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec	
Temperature (t _P)			
Ramp-down Rate	<6°C/sec	<6°C/sec	
Time 25°C to Peak Temperature	<6 minutes	<8 minutes	

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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